# UNISONIC TECHNOLOGIES CO., LTD

6NM70-Q **Preliminary** Power MOSFET

# 6.0A, 700V N-CHANNEL SUPER-JUNCTION MOSFET

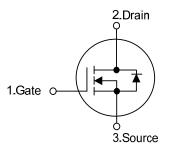
#### DESCRIPTION

The UTC 6NM70-Q is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

#### **FEATURES**

- \*  $R_{DS(ON)}$  < 1.44 $\Omega$  @  $V_{GS}$  = 10V,  $I_{D}$  =3.0A
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability, high ruggedness

## **SYMBOL**

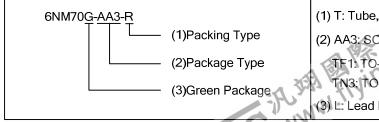


# SOT-223 TO-220 TO-220F TO-220F1 TO-220F2 TO-251 TO-252

#### ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Doolsing
Lead Free	Halogen Free	Package	1	2	3	Packing
-	6NM70G-AA3-R	SOT-223	G	D	S	Tape Reel
6NM70L-TA3-T	6NM70G-TA3-T	TO-220	G	D	S	Tube
6NM70L-TF3-T	6NM70G-TF3-T	TO-220F	G	D	S	Tube
6NM70L-TF1-T	6NM70G-TF1-T	TO-220F1	G	D	S	Tube
6NM70L-TF2-T	6NM70G-TF2-T	TO-220F2	G	D	S	Tube
6NM70L-TM3-T	6NM70G-TM3-T	TO-251	G	D	S	Tube
6NM70L-TN3-R	6NM70G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain



- (1) T: Tube, R: Tape Ree
- (2) AA3: SOT-223, TA3: TO-220, TF3: TO-220F,
  - TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251,
- (3) L: Lead Free, G: Halogen Free and Lead Free

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### **MARKING**

SOT-223	TO-220 / TO-220F / TO-220F1 TO-220F2 / TO-251 / TO-252			
6NM70G  Lot Code	UTC 6NM70□ C: Lead Free G: Halogen Free Data Code			



### ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>C</sub> = 25°C, unless otherwise specified)

PARA	PARAMETER		RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	700	V
Gate-Source Voltage		$V_{GSS}$	±30	V
Drain Current	Continuous	$I_{D}$	6.0	Α
Drain Current	Pulsed (Note 2)	$I_{DM}$	24	Α
Avalanche Current (Note	2)	I <sub>AR</sub> 1.3		Α
Avalanche Energy	Single Pulsed (Note 3)	E <sub>AS</sub>	123	mJ
Peak Diode Recovery dv	/dt (Note 4)	dv/dt	3.9	V/ns
rain-Source Voltage late-Source Voltage rain Current valanche Current (Note 2 valanche Energy eak Diode Recovery dv/d ower Dissipation	SOT-223		5	W
	TO-220	P <sub>D</sub>	125	W
Power Dissipation	TO-220F/TO-220F1 TO-220F2		40	W
	TO-251/TO-252		55	W
Junction Temperature	Junction Temperature		+150	°C
Storage Temperature		$T_{STG}$	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L=145mH,  $I_{AS}$ =1.3A,  $V_{DD}$ =50V,  $R_{G}$ =25  $\Omega$ , Starting  $T_{J}$  = 25°C
- 4.  $I_{SD} \le 6.0A$ , di/dt $\le 200A/\mu s$ ,  $V_{DD} \le BV_{DSS}$ , Starting  $T_J = 25^{\circ}C$

#### **■ THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT	
Junction to Ambient	SOT-223		150	°C/W	
	TO-220/TO-220F TO-220F1/TO-220F2	$\theta_{JA}$	62.5		
	TO-251/TO-252		110		
Junction to Case	SOT-223		25	°C/W	
	TO-220		1.0		
	TO-220F/TO-220F1 TO-220F2	θ <sub>JC</sub>	3.13		
	TO-251/TO-252		2.27		



### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> =25°C, unless otherwise specified)

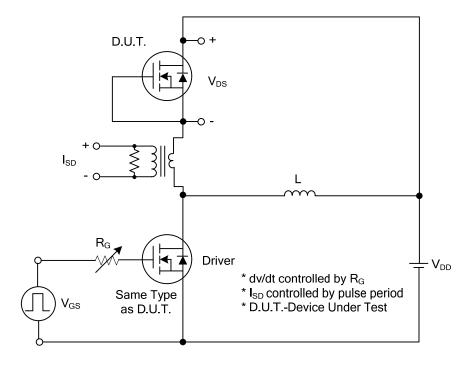
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	700			V
Drain-Source Leakage Current	Orain-Source Leakage Current		$V_{DS} = 700V, V_{GS} = 0V$			10	μΑ
Gate-Source Leakage Current	Forward	Cee	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
	Reverse		$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5		4.5	V
Static Drain-Source On-State Res	Static Drain-Source On-State Resistance		$V_{GS} = 10V, I_D = 3.0A$			1.44	Ω
DYNAMIC CHARACTERISTICS	_	-					
Input Capacitance	nput Capacitance		V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f =1MHz		330		pF
Output Capacitance		Coss			215		pF
Reverse Transfer Capacitance		$C_{RSS}$			20		pF
SWITCHING CHARACTERISTICS	S			a			
Total Gate Charge (Note 1)		$Q_{G}$	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =1.3A		50		nC
Gate to Source Charge		$Q_GS$			4.0		nC
Gate to Drain Charge		$Q_GD$	-I <sub>G</sub> =100μA (Note 1, 2)		11		nC
Turn-ON Delay Time (Note 1)		t <sub>D (ON)</sub>			36		ns
Rise Time		$t_R$	$V_{DD}$ =30V, $V_{GS}$ =10V, $I_{D}$ =0.5A,		65		ns
Turn-OFF Delay Time		$t_{D(OFF)}$	R <sub>G</sub> =25Ω (Note 1, 2)		140		ns
Fall-Time		$t_{F}$			45		ns
SOURCE- DRAIN DIODE RATING	GS AND CH	ARACTERIS	TICS	ā			
Maximum Body-Diode Continuous	Current	$I_S$				6.0	Α
Maximum Body-Diode Pulsed Cur	rent	I <sub>SM</sub>				24	Α
Drain-Source Diode Forward Volta	age (Note 1)	$V_{SD}$	I <sub>S</sub> =6.0A, V <sub>GS</sub> =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t <sub>rr</sub>	I <sub>S</sub> =6.0A, V <sub>GS</sub> =0V,		310		nS
Body Diode Reverse Recovery Charge		$Q_{rr}$	dI <sub>F</sub> /dt=200A/µs		2.7		μC

Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle≤2%.

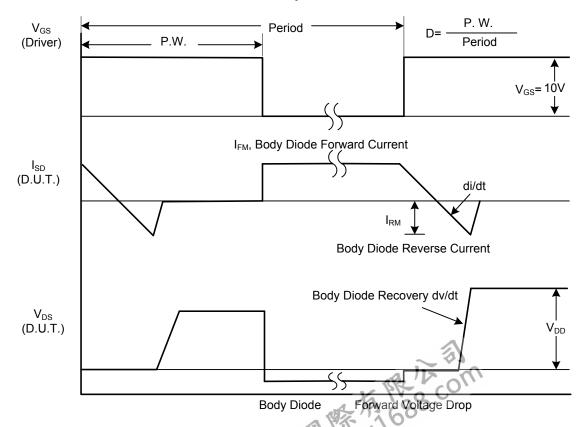


<sup>2.</sup> Essentially independent of operating temperature.

#### ■ TEST CIRCUITS AND WAVEFORMS

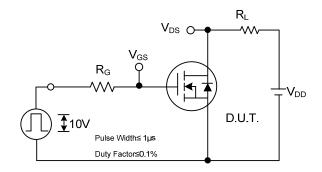


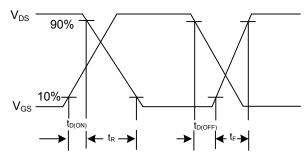
### Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Waveforms

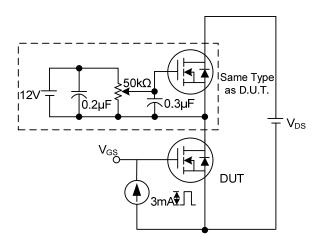
## **TEST CIRCUITS AND WAVEFORMS (Cont.)**

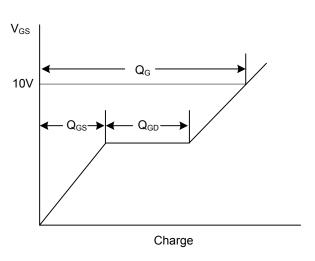




**Switching Test Circuit** 

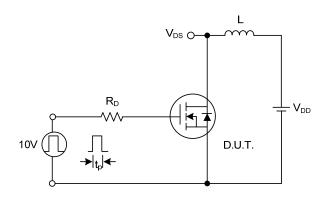
**Switching Waveforms** 

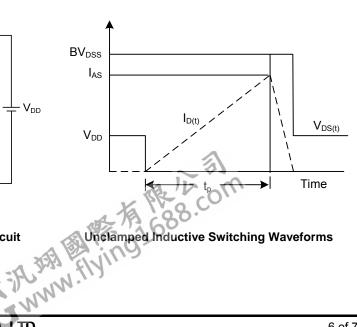




**Gate Charge Test Circuit** 

**Gate Charge Waveform** 





**Unclamped Inductive Switching Test Circuit** 

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